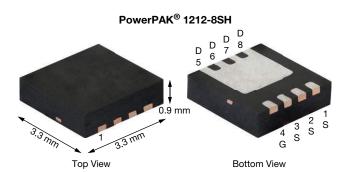
Vishay Siliconix

N-Channel 20 V (D-S) Fast Switching MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	20
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0062
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 2.5 \text{ V}$	0.0098
Q _g typ. (nC)	17.5
I _D (A)	19.5
Configuration	Single

FEATURES

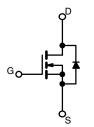
- TrenchFET® power MOSFET
- 2.5 V rated R_{DS(on)}
- PWM optimized
- 100 % Ra tested

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



APPLICATIONS

- Synchronous rectification
- · Load switch



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH106DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T	A = 25 °C, unle	ss otherwise r	noted)			
PARAMETER	SYMBOL	10 s	STEADY STATE	UNIT		
Drain-source voltage		V _{DS}	20	20	V	
Gate-source voltage		V _{GS} ± 12		± 12	V	
Continuous drain surrent (T. – 150 °C) 8	T _A = 25 °C	I-	19.5	12.5		
Continuous drain current (T _J = 150 °C) ^a	T _A = 70 °C	I _D	15.6	10		
Pulsed drain current		I _{DM}	60	60	А	
Continuous source current (diode conduction) a		I _S	3.2	1.3		
Single avalanche current	L = 0.1 mH	I _{AS}	30	30		
Single avalanche energy	L=0.1 min	E _{AS}	45	45	mJ	
Maximum namer discipation 8	T _A = 25 °C	Б	3.8	1.5	w	
Maximum power dissipation ^a	T _A = 70 °C	P _D	2	0.8		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150		°C	
Soldering recommendations (peak temperature) b, c			260		l	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction to ambient 8	t ≤ 10 s	D	24	33	°C/W
Maximum junction-to-ambient ^a	Steady state	R_{thJA}	65	81	
Maximum junction-to-case (drain)	Steady state	R _{thJC}	1.9	2.4	

Notes

- a. Surface mounted on 1" x 1" FR4 board
- b. See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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SPECIFICATIONS (T _J = 25 °C	C, unless otl	herwise noted)					
PARAMETER	SYMBOL	YMBOL TEST CONDITIONS		TYP.	MAX.	UNIT	
Static							
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.6	-	1.5	V	
Gate-body leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$	-	-	± 100	nA	
Zoro gato voltago drain current	l	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1		
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	5	μA	
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	40	-	-	Α	
Drain acurae en etete registance a	В	$V_{GS} = 4.5 \text{ V}, I_D = 19.5 \text{ A}$	-	0.0051	0.0062		
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 15.5 \text{ A}$	-	0.0081	0.0098	Ω	
Forward transconductance a	9 _{fs}	V _{DS} = 15 V, I _D = 19.5 A	-	105	-	S	
Diode forward voltage a	V _{SD}	$I_S = 3.2 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.8	1.2	V	
Dynamic ^b							
Total gate charge	Qg		-	17.5	27		
Gate-source charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 19.5 \text{ A}$	-	6.6	-	nC	
Gate-drain charge	Q_{gd}		-	2.8	-		
Gate resistance	R_g	f = 1 MHz	0.7	1.4	2.1	Ω	
Turn-on delay time	t _{d(on)}		-	25	40		
Rise time	t _r	V_{DD} = 10 V, R_L = 10 Ω	-	15	25		
Turn-off delay time	t _{d(off)}	$I_D \cong 1$ A, $V_{GEN} = 10$ V, $R_g = 6$ Ω	-	50	75	ns	
Fall time	t _f		-	12	20		
Source-drain reverse recovery time	t _{rr}	I _F = 3.2 A, di/dt = 100 A/μs	-	30	60		

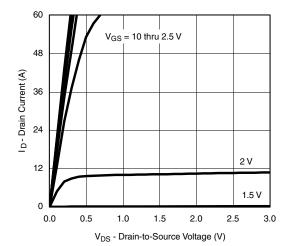
Notes

- a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

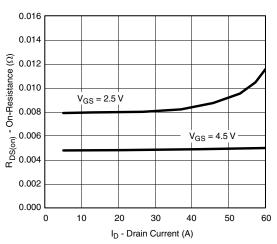
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



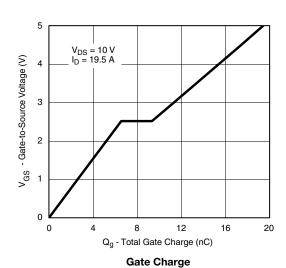
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

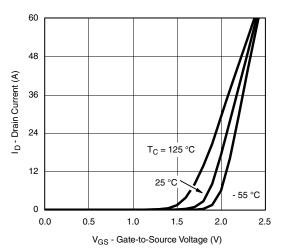


Output Characteristics

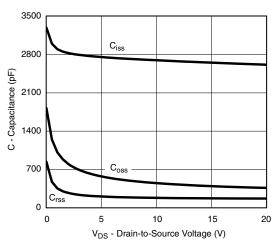


On-Resistance vs. Drain Current

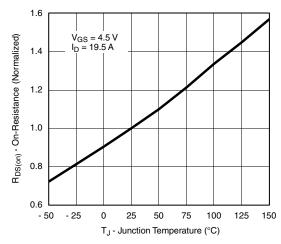




Transfer Characteristics



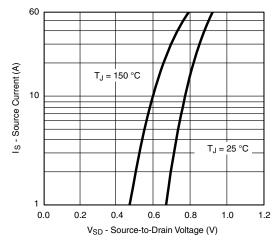
Capacitance



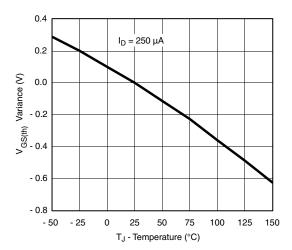
On-Resistance vs. Junction Temperature



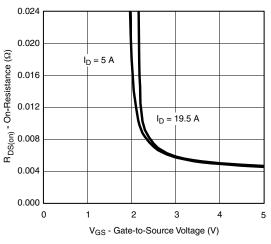
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



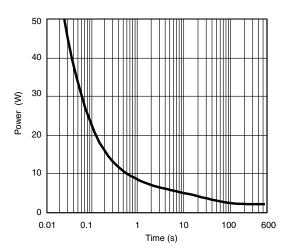
Source-Drain Diode Forward Voltage



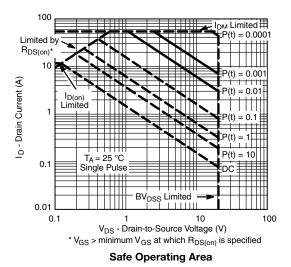
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

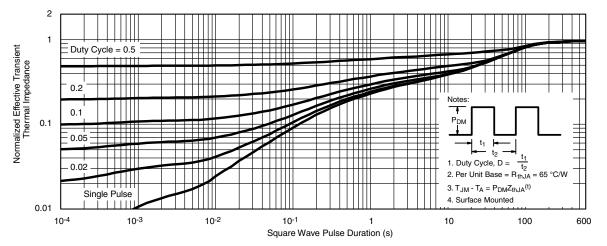


Single Pulse Power, Junction-to-Ambient

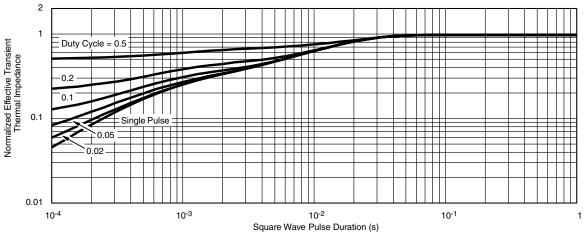




TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

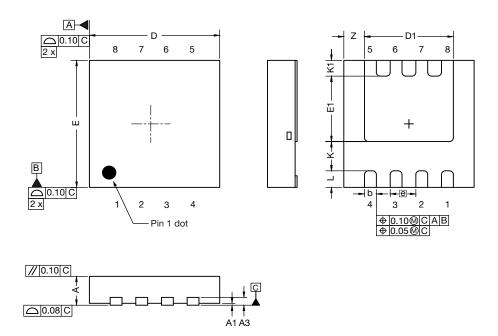


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?79358.

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Case Outline for PowerPAK® 1212-SWLH and PowerPAK® 1212-8SH

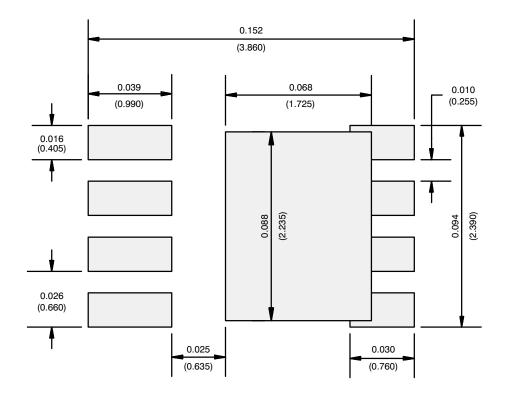


DIM.		MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.82	0.90	0.98	0.032	0.035	0.038	
A1	0.00	-	0.05	0.000	-	0.002	
A3		0.20 ref.			0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.15	2.25	2.35	0.085	0.089	0.093	
Е	3.20	3.30	3.40	0.126	0.130	0.134	
E1	1.60	1.70	1.80	0.063	0.067	0.071	
е		0.65 bsc.			0.026 bsc.		
K		0.76 ref.			0.030 ref.		
K1	0.41 ref.		0.016 ref.				
L	0.33	0.43	0.53	0.013	0.017	0.021	
Z	0.525 ref.			0.021 ref.			
	Rev. C, 07-Dec-2020					0.021 ref.	

DWG: 6062



RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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